



DMN3033LSN

N-CHANNEL ENHANCEMENT MODE MOSFET

Features

- Low Gate Charge
- Low R_{DS(ON)}:
 - 30 mΩ @V_{GS} = 10V
- 40 m Ω @V_{GS} = 4.5V
- Low Input/Output Leakage
- Lead Free By Design/RoHS Compliant (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability
- "Green" Device (Note 4)

Mechanical Data

- Case: SC-59
- Case Material Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin annealed over Copper leadframe. Solderable per MIL-STD-202, Method 208
- Terminal Connections: See Diagram
- Marking Information: See Page 4
- Ordering Information: See Page 4
- Weight: 0.014 grams (approximate)

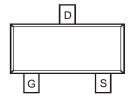


Top View



Drain

Equivalent Circuit



Pin Configuration

Maximum Ratings @T_A = 25°C unless otherwise specified

Characteristic		Symbol	Value	Unit
Drain-Source Voltage		V _{DSS}	30	V
Gate-Source Voltage		V _{GSS}	±20	V
Drain Current (Note 1) Continuous	T _A = 25°C T _A = 70°C	Ι _D	6 5	А
Pulsed Drain Current (Note 2)		I _{DM}	24	A
Body-Diode Continuous Current (Note 1)		Is	2.25	A

Thermal Characteristics @T_A = 25°C unless otherwise specified

Characteristic	Symbol	Value	Unit
Total Power Dissipation (Note 1)	PD	1.4	W
Thermal Resistance, Junction to Ambient (Note 1) t ≤10s	R _{θJA}	90	°C /W
Operating and Storage Temperature Range	T _J , T _{STG}	-55 to +150	°C

Notes: 1. Device mounted on 1"x1", FR-4 PC board with 2 oz. Copper and test pulse width t \leq 10s.

2. Repetitive Rating, pulse width limited by junction temperature.

3. No purposefully added lead.

4. Diodes Inc's "Green" policy can be found on our website at http://www.diodes.com/products/lead_free/index.php.

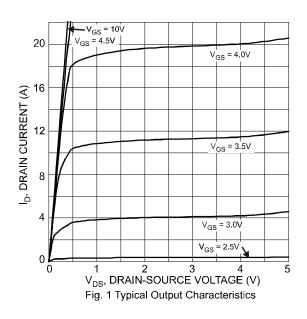


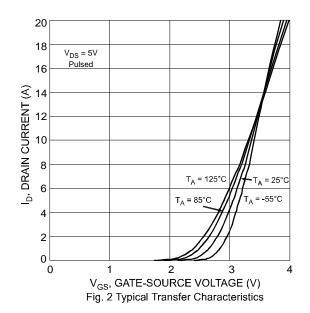
Electrical Characteristics @T_A = 25°C unless otherwise specified

Characteristic		Symbol	Min	Тур	Мах	Unit	Test Condition
STATIC PARAMETERS		Cymbol		- IJP	max	Unit	
Drain-Source Breakdown Voltage	BV _{DSS}	30	_	—	V	$I_{D} = 250 \mu A, V_{GS} = 0 V$	
Zero Gate Voltage Drain Current	T _J = 25°C T _J = 55°C	I _{DSS}	_	_	1 5	μΑ	$V_{DS} = 30V, V_{GS} = 0V$
Gate-Body Leakage Current		I _{GSS}	_		±100	nA	$V_{DS} = 0V, V_{GS} = \pm 20V$
Gate Threshold Voltage		V _{GS(th)}	1.0		2.1	V	$V_{DS} = V_{GS}, I_D = 250 \mu A$
Static Drain-Source On-Resistance (Note 5)	R _{DS (ON)}	_	25 36	30 40	mΩ	$V_{GS} = 10V, I_D = 6A$ $V_{GS} = 4.5V, I_D = 5A$	
Forward Transconductance (Note 5)			_	5	_	S	$V_{DS} = 10V, I_D = 8A$
Diode Forward Voltage (Note 5)			_	0.7	1.1	V	I _S = 2.25A, V _{GS} = 0V
DYNAMIC PARAMETERS (Note 6)							
Total Gate Charge		Qg	_	10.5		nC	$V_{GS} = 5V, V_{DS} = 15V, I_D = 6A$
Gate-Source Charge		Q _{gs}	_	3.8		nC	$V_{GS} = 10V, V_{DS} = 15V, I_D = 6A$
Gate-Drain Charge		Q _{gd}	_	2.9		nC	$V_{GS} = 10V, V_{DS} = 15V, I_D = 6A$
Turn-On Delay Time		t _{D(on)}	_	11	—	ns	
Turn-On Rise Time		tr	_	7	_	ns	V _{DD} = 15V, V _{GS} = 10V,
Turn-Off Delay Time		t _{D(off)}	_	63		ns	$R_D = 1.8\Omega, R_G = 6\Omega$
Turn-Off Fall Time		t _f		30		ns	
Input Capacitance		Ciss	_	755	_	pF	
Output Capacitance		Coss	_	136		pF	−V _{DS} = 10V, V _{GS} = 0V −f = 1.0MHz
Reverse Transfer Capacitance		C _{rss}	_	108		pF	

Notes: 5. Test pulse width t = 300ms.

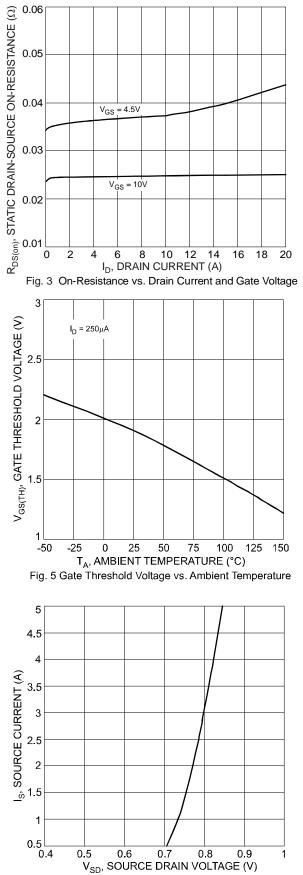
6. Guaranteed by design. Not subject to production testing.

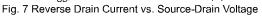


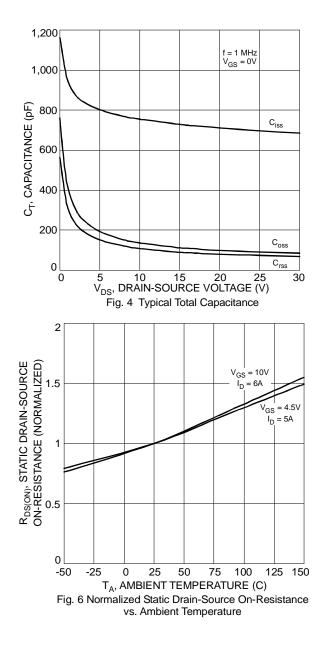












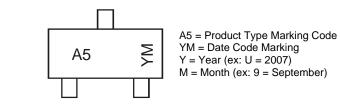


Ordering Information (Note 7)

Part Number	Case	Packaging
DMN3033LSN-7	SC-59	3000/Tape & Reel

Notes: 7. For packaging details, go to our website at http://www.diodes.com/datasheets/ap02007.pdf.

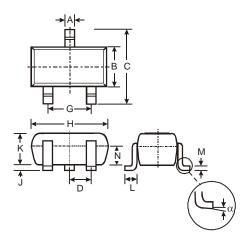
Marking Information



Date	Code	Kev	

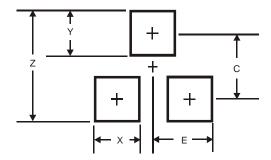
Year	2007	20	08	2009	2010	20	11	2012	2013	20	14	2015
Code	U	١	/	W	Х	``	Y	Z	А	E	3	С
Month	Jan	Feb	Mar	Apr	Мау	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	0	N	D

Package Outline Dimensions



SC-59							
Dim	Min	Max	Тур				
Α	0.35	0.50	0.38				
В	1.50	1.70	1.60				
С	2.70	3.00	2.80				
D	-	-	0.95				
G	-	-	1.90				
н	2.90	3.10	3.00				
J	0.013	0.10	0.05				
κ	1.00	1.30	1.10				
L 0.35		0.55	0.40				
М	0.10	0.20	0.15				
Ν	0.70	0.80	0.75				
α	0°	8°	-				
All	Dimens	ions in	mm				

Suggested Pad Layout



Dimensions	Value (in mm)
Z	3.4
Х	0.8
Y	1.0
С	2.4
E	1.35



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